

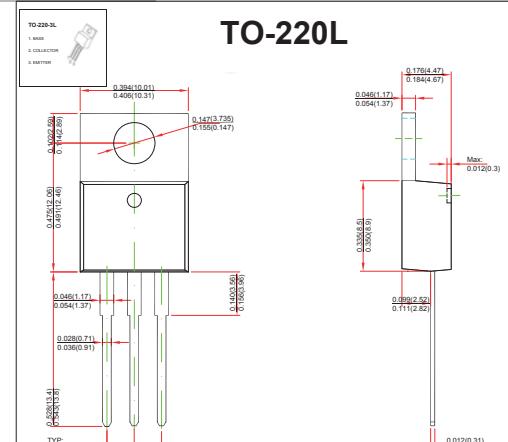
TO-220L Plastic-Encapsulate Transistors

FEATURES

- High Current Switching Applications
- Low Collector Saturation Voltage
- High Speed Swithing Time
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style: TO-220L molded plastic
- Mounting position: any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _c	Collector Current -Continuous	-5	A
P _c	Collector Power Dissipation	2	W
R _{θJA}	Thermal Resistance Junction to Ambient	62.5	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~+150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SA1012	TO-220L	50/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =-0.1mA, I _e =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _c =-10mA, I _b =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _e =-100μA, I _c =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _e =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _c =0			-1	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _c =-1A	70		240	
	h _{FE(2)*}	V _{CE} =-1V, I _c =-3A	30			
Collector-emitter saturation voltage	V _{CE(sat)*}	I _c =-3A, I _b =-150mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)*}	I _c =-3A, I _b =-150mA			-1.2	V
Transition frequency	f _T	V _{CE} =-4V, I _c =-1A		60		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _e =0, f=1MHz		170		pF
Turn-on Time	t _{on}	V _{CC} =-30V, I _c =-3A, I _{b1} =-I _{b2} =-0.15A		0.1		
Storage Time	t _s			1.0		μs
Fall Time	t _f			0.1		

*Pulse test: t_p≤300μs, δ≤0.02.

CLASSIFICATION of h_{FE(1)}

Rank	O	Y
Range	70-140	120-240